## ELECTRON BEAM SYSTEM

## ABSTRACT OF THE DISCLOSURE

Provided is an electron beam system, in which an electron beam emitted from an electron gun is irradiated to a stencil mask, and the electron beam that has passed through the stencil mask is magnified by an electron lens and then detected by a detector having a plurality of pixels so as to form an image of the sample.

Further, an etching apparatus for a sample such as a

10 wafer and a stencil mask includes an inspection apparatus
incorporated therein. The etching apparatus further
comprises a load unit, a pattern forming unit, a cleaning
unit, a drying unit and an unload unit. The etching
apparatus receives the sample from a preceding step,

15 applies respective processing to the sample by said
respective units, and then transfers the processed sample
to a subsequent step. A sample loading means, a sample
unloading means and a transport means are not required for
the transfer of the sample between respective units.

Since the beam in a sheet-like configuration is irradiated to the stencil mask from its reverse side, and the transmission beam is image-projected and detected by a TDI detector, therefore a large number of pixels are imaged at the same time, thereby enabling an inspection with a high throughput.

Further, the present invention provides an electron beam system, in which a primary electron beam emitted from an electron gun is directed to a sample surface of a

sample prepared as a subject to be inspected, and an electron image formed by a secondary electron beam emanated from the sample is magnified and detected, wherein an NA aperture is disposed on the path common to both of said primary electron beam and said secondary electron beam, an electron lens is disposed in the vicinity of said sample surface, and in this arrangement, a crossover produced by said electron gun, said electron lens and said NA aperture may be in the conjugate relationships to each other with respect to said primary electron beam.

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